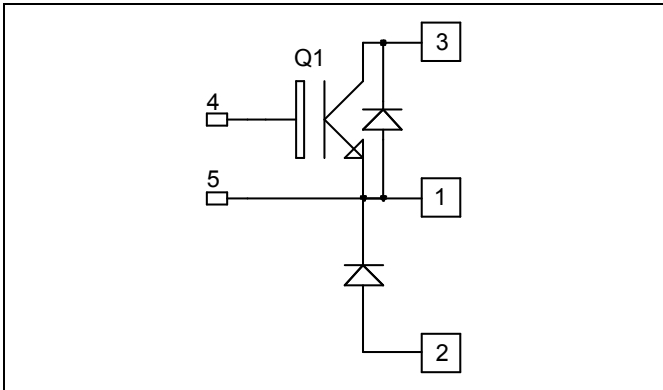


## Buck Chopper NPT IGBT Power Module

$V_{CES} = 600V$   
 $I_C = 330A @ T_c = 80^\circ C$

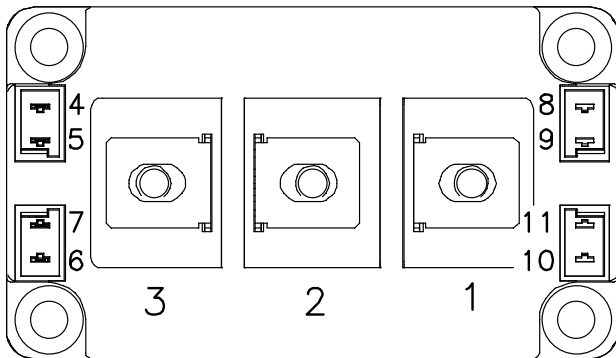


### Application

- AC and DC motor control
- Switched Mode Power Supplies

### Features

- Non Punch Through (NPT) FAST IGBT
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors



### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	520
		$T_C = 80^\circ C$	330
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	800
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	1560
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	800A @ 520V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.  
 See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}, V_{CE} = 600\text{V}$			500	$\mu\text{A}$
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 400\text{A}$	$T_j = 25^\circ\text{C}$	1.95	2.45	V
			$T_j = 125^\circ\text{C}$	2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 7.5\text{ mA}$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			1200	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0\text{V}; V_{CE} = 25\text{V}$		18		nF
$C_{res}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		1.6		
$Q_G$	Gate charge	$V_{GE}=15\text{V}, I_C=400\text{A}$ $V_{CE}=300\text{V}$		1.3		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ )		150		ns
$T_r$	Rise Time	$V_{GE} = \pm 15\text{V}$		72		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300\text{V}$ $I_C = 400\text{A}$		530		
$T_f$	Fall Time	$R_G = 8\Omega$		40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ )		160		ns
$T_r$	Rise Time	$V_{GE} = \pm 15\text{V}$		75		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300\text{V}$ $I_C = 400\text{A}$		550		
$T_f$	Fall Time	$R_G = 8\Omega$		50		
$E_{on}$	Turn on Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$	$T_j = 125^\circ\text{C}$	18		mJ
$E_{off}$	Turn off Energy	$I_C = 400\text{A}$ $R_G = 8\Omega$	$T_j = 125^\circ\text{C}$	17		
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15\text{V}; V_{Bus} = 360\text{V}$ $t_b \leq 10\mu\text{s}; T_j = 125^\circ\text{C}$		1800		A

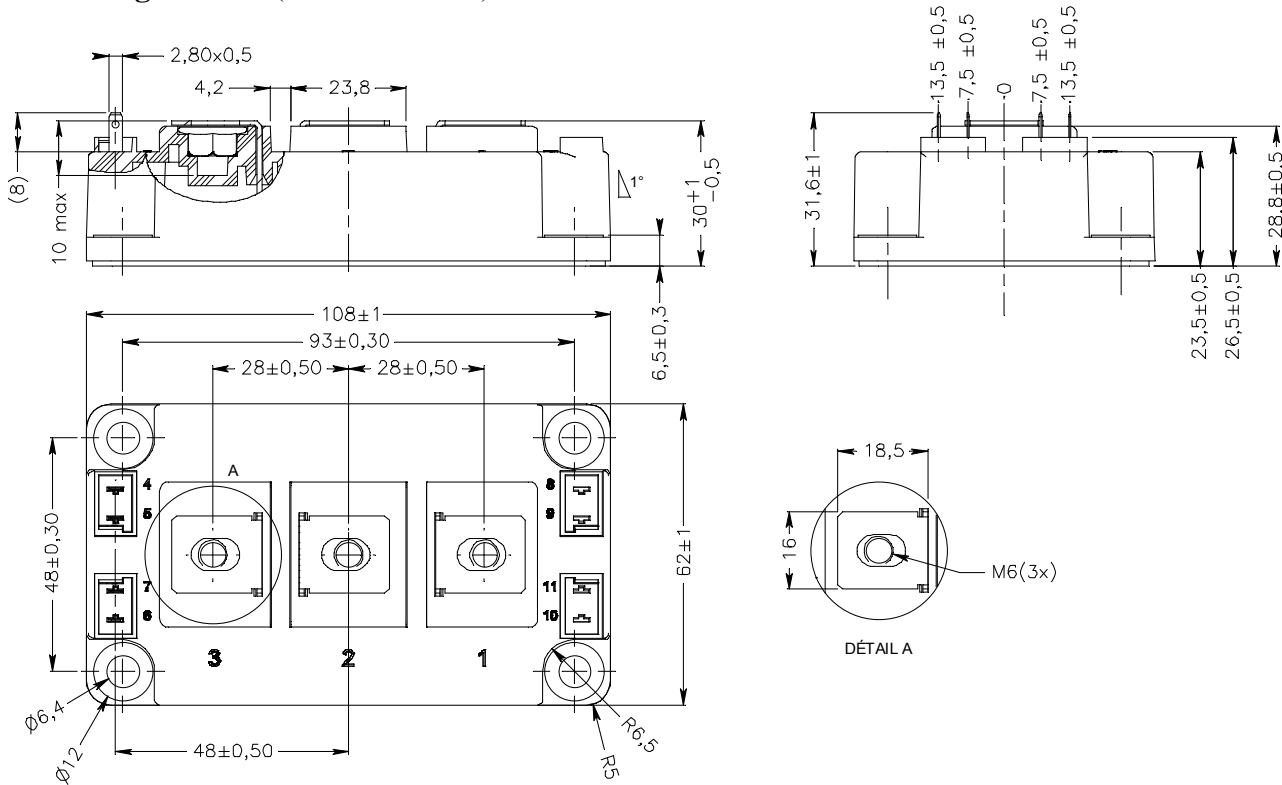
**Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RRM}$	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		750	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		1000	
$I_F$	DC Forward Current		$T_c = 80^\circ\text{C}$	400		A
$V_F$	Diode Forward Voltage	$I_F = 400\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$	1.25	1.6	V
			$T_j = 125^\circ\text{C}$	1.2		
$t_{rr}$	Reverse Recovery Time		$T_j = 25^\circ\text{C}$	150		ns
			$T_j = 125^\circ\text{C}$	250		
$Q_{rr}$	Reverse Recovery Charge	$I_F = 400\text{A}$ $V_R = 300\text{V}$ $di/dt = 4400\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$	27		$\mu\text{C}$
			$T_j = 125^\circ\text{C}$	44		
$E_{rr}$	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$	5.6		mJ
			$T_j = 125^\circ\text{C}$	9.2		

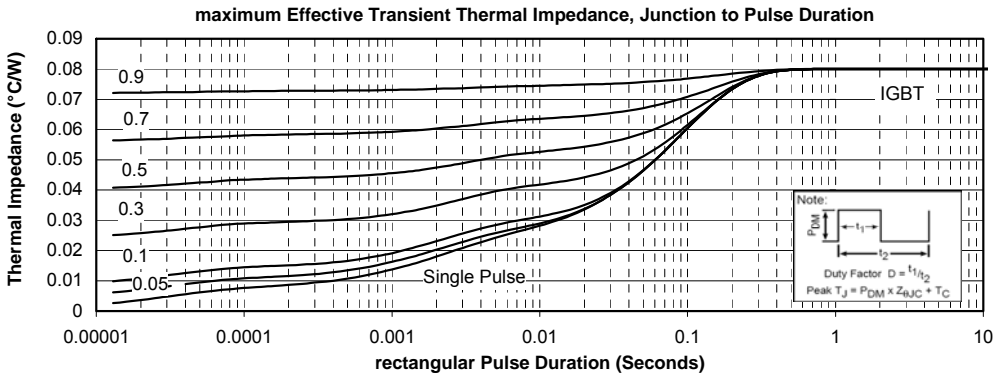
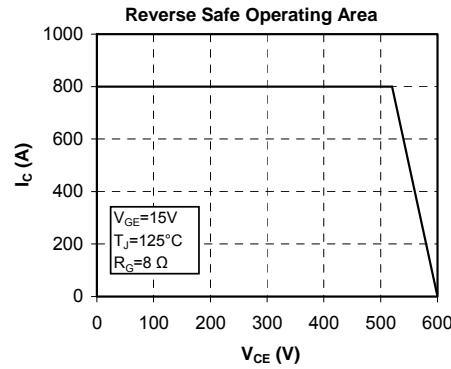
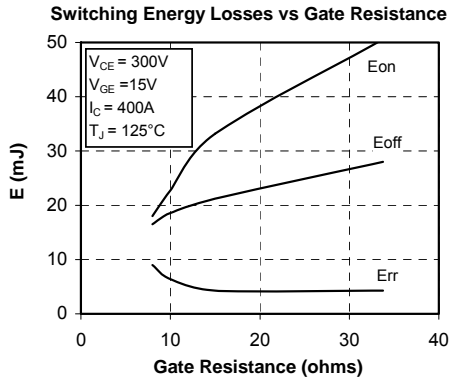
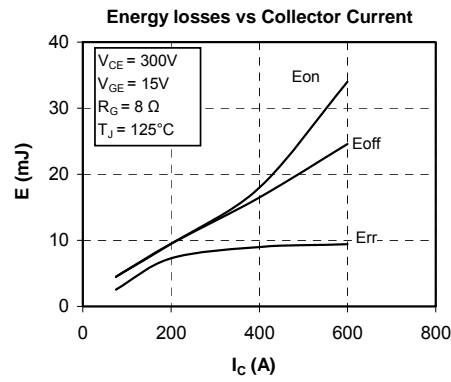
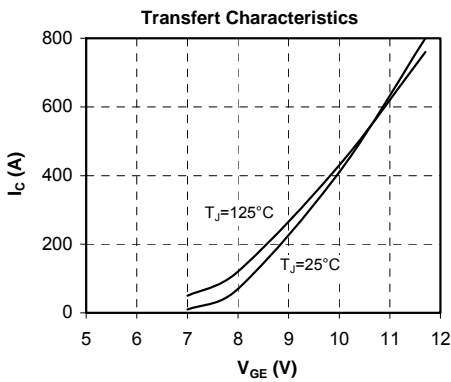
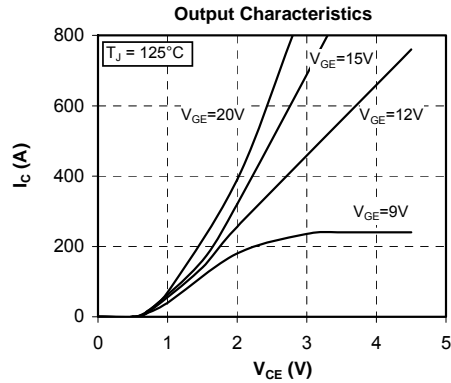
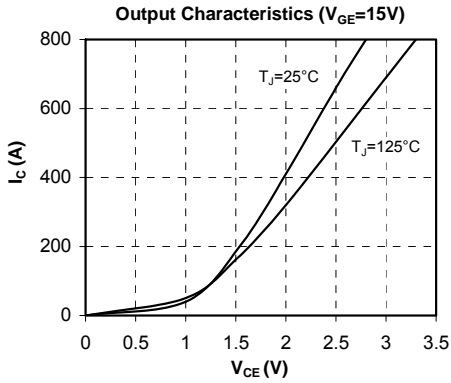
## Thermal and package characteristics

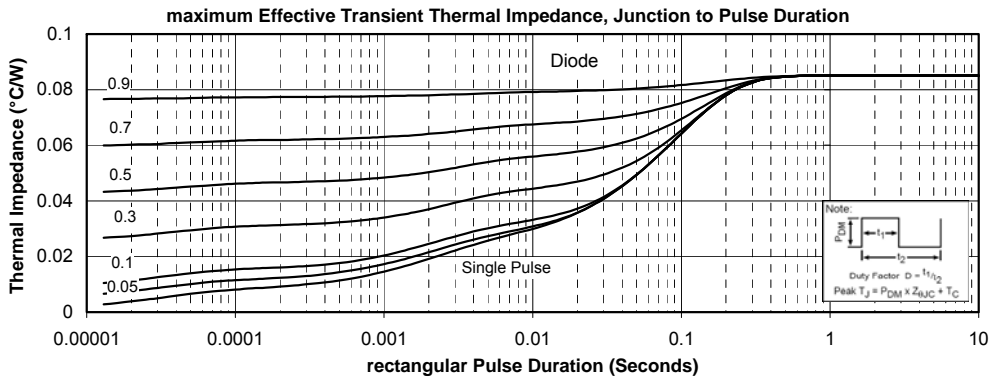
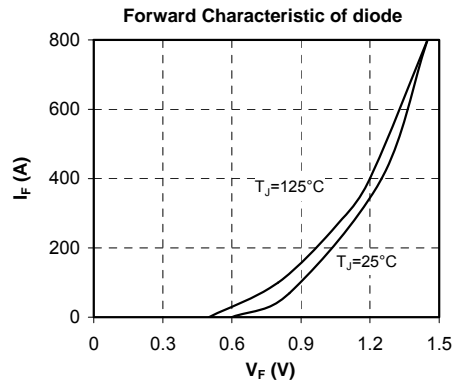
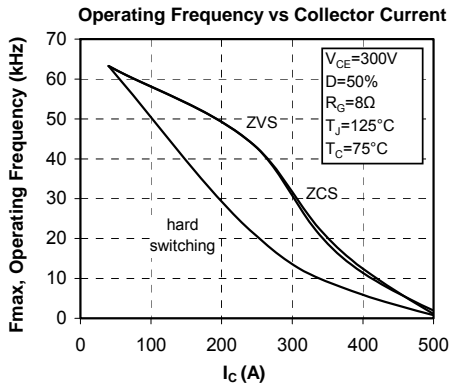
Symbol	Characteristic	Min	Typ	Max	Unit	
$R_{thJC}$	Junction to Case Thermal Resistance	IGBT		0.08	°C/W	
		Diode		0.15		
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{isol}<1$ mA, 50/60Hz	2500			V	
$T_J$	Operating junction temperature range	-40		150	°C	
$T_{STG}$	Storage Temperature Range	-40		125		
$T_C$	Operating Case Temperature	-40		125		
Torque	Mounting torque	For terminals	M6	3	5	N.m
		To Heatsink	M6	3	5	
Wt	Package Weight			350	g	

## D3 Package outline (dimensions in mm)



## Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

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